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Kind regards,

Team Nexperia



PESD5V0U2BT

Ultra low capacitance bidirectional double ESD protection diode

Rev. 01 — 27 March 2007

Product data sheet

Product profile 1.

1.1 General description

Ultra low capacitance bidirectional double ElectroStatic Discharge (ESD) protection diode in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package designed to protect two data lines from the damage caused by ESD.

1.2 Features

- Bidirectional ESD protection of two lines Ultra low leakage current: I_{RM} = 5 nA

Subscriber Identity Module (SIM) card

Ultra low diode capacitance: C_d = 2.9 pF E ESD protection of up to 10 kV

Communication systems

Portable electronics

High-speed data lines

protection

FireWire

IEC 61000-4-2; level 4 (ESD)

1.3 Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- 10/100/1000 Ethernet
- Local Area Network (LAN) equipment

1.4 Quick reference data

 Table 1.
 Quick reference data

$I_{amb} = 25^{\circ}$	C unless otherwise specifi	ed.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
V _{RWM}	reverse standoff voltage	e	-	-	5	V
C _d	diode capacitance	f = 1 MHz; V _R = 0 V	-	2.9	3.5	рF



2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	cathode 1	<u> </u>	
2	cathode 2		
3	common cathode		
			006aaa155

3. Ordering information

Table 3. Order	ing information	on	
Type number	Package		
	Name	Description	Version
PESD5V0U2BT	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4.	Marking codes	
Type num	nber	Marking code ^[1]
PESD5V0)U2BT	1U*

[1] * = -: made in Hong Kong

- * = p: made in Hong Kong
- * = t: made in Malaysia
- * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Table 6.ESD maximum ratings

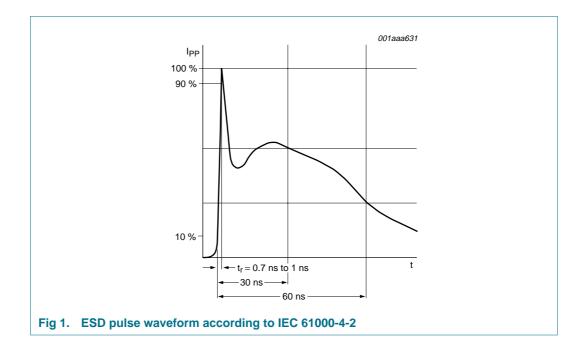
Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V_{ESD}	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	10	kV
		MIL-STD-883 (human body model)		-	8	kV

[1] Device stressed with ten non-repetitive ESD pulses.

[2] Measured from pin 1 to pin 2.

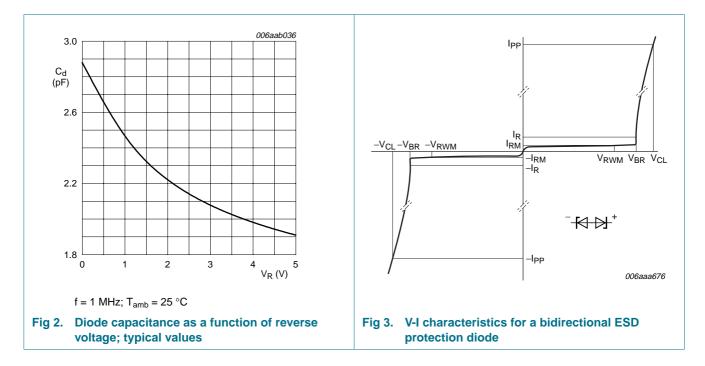
Table 7. ESD standards compliance

Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV



6. Characteristics

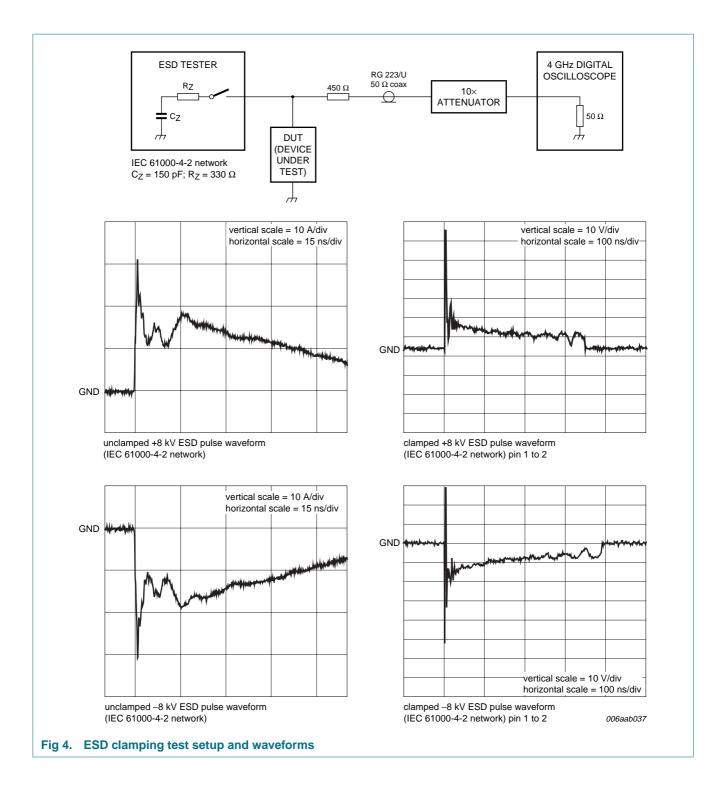
	Characteristics Cunless otherwise specified	d.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
V _{RWM}	reverse standoff voltage		-	-	5	V
I _{RM}	reverse leakage current	$V_{RWM} = 5 V$	-	5	100	nA
V _{BR}	breakdown voltage	I _R = 5 mA	5.5	7	9.5	V
C _d	diode capacitance	f = 1 MHz				
		$V_R = 0 V$	-	2.9	3.5	pF
		$V_R = 5 V$	-	1.9	-	pF
r _{dif}	differential resistance	I _R = 1 mA	-	-	100	Ω



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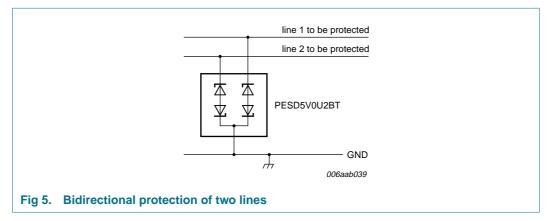
PESD5V0U2BT

Ultra low capacitance bidirectional double ESD protection diode



7. Application information

The PESD5V0U2BT is designed for the bidirectional protection of two signal lines from the damage caused by ESD pulses. The PESD5V0U2BT may be used on lines where the signal polarities are either positive or negative with respect to ground.



Circuit board layout and protection device placement

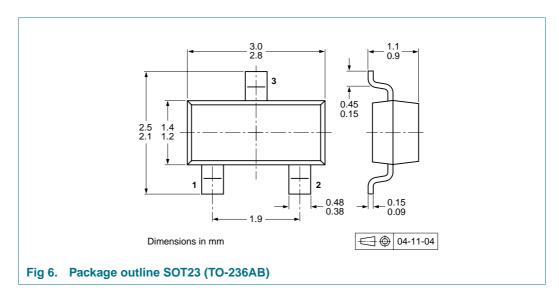
Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the PESD5V0U2BT as close to the input terminal or connector as possible.
- 2. The path length between the PESD5V0U2BT and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

PESD5V0U2BT

Ultra low capacitance bidirectional double ESD protection diode

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

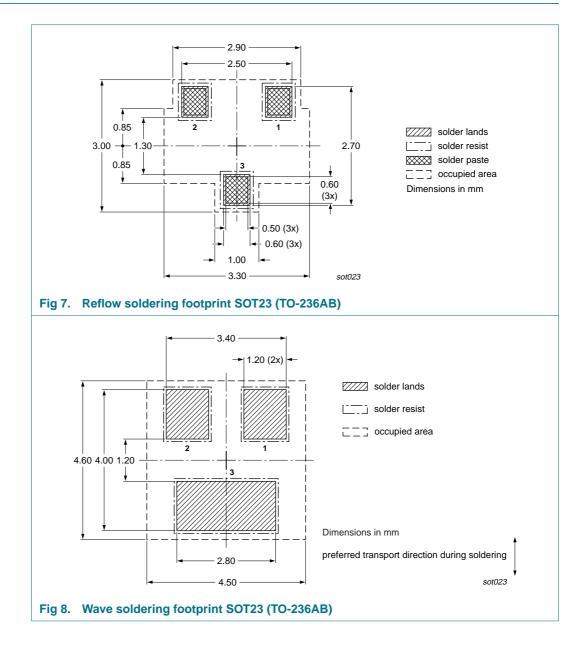
Type number	Package	Description Packing qu		quantity	
			3000	10000	
PESD5V0U2BT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

PESD5V0U2BT

Ultra low capacitance bidirectional double ESD protection diode

10. Soldering



11. Revision history

Table 10. Revision histor	У			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD5V0U2BT_1	20070327	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PESD5V0U2BT

Ultra low capacitance bidirectional double ESD protection diode

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